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Should be replaced with:

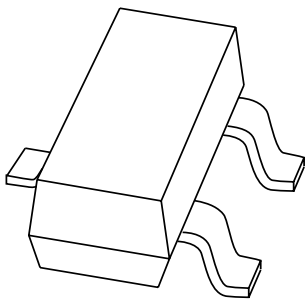
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DATA SHEET



**BCW89**

**PNP general purpose transistor**

Product data sheet  
Supersedes data of 1997 Mar 11

1999 Apr 15

# PNP general purpose transistor

# BCW89

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 60 V).

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

PNP transistor in a SOT23 plastic package.

### MARKING

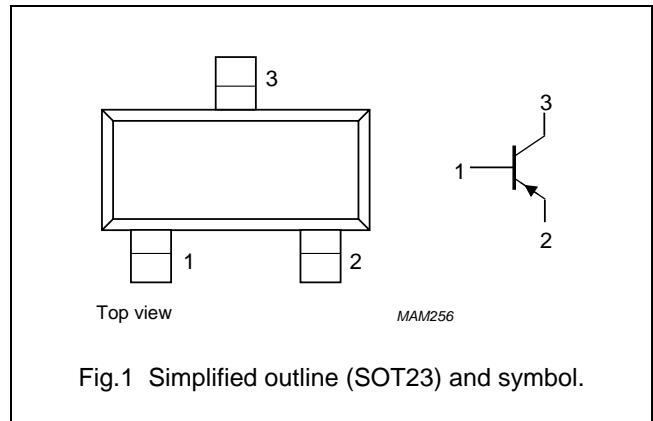
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BCW89	H3*

### Note

- \* = p : Made in Hong Kong.  
\* = t : Made in Malaysia.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	–80	V
V <sub>CEO</sub>	collector-emitter voltage	open base; I <sub>C</sub> = –2 mA	–	–60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–5	V
I <sub>C</sub>	collector current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–200	mA
I <sub>BM</sub>	peak base current		–	–200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

## PNP general purpose transistor

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -20\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -20\text{ V}; T_j = 100\text{ °C}$	–	–	–10	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
$h_{FE}$	DC current gain	$I_C = -10\text{ }\mu\text{A}; V_{CE} = -5\text{ V}$	–	90	–	
		$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	120	–	260	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–80	–300	mV
		$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}$	–	–150	–	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–720	–	mV
		$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}$	–	–810	–	mV
$V_{BE}$	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	–600	–	–750	mV
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	4.5	–	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	–	150	–	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB

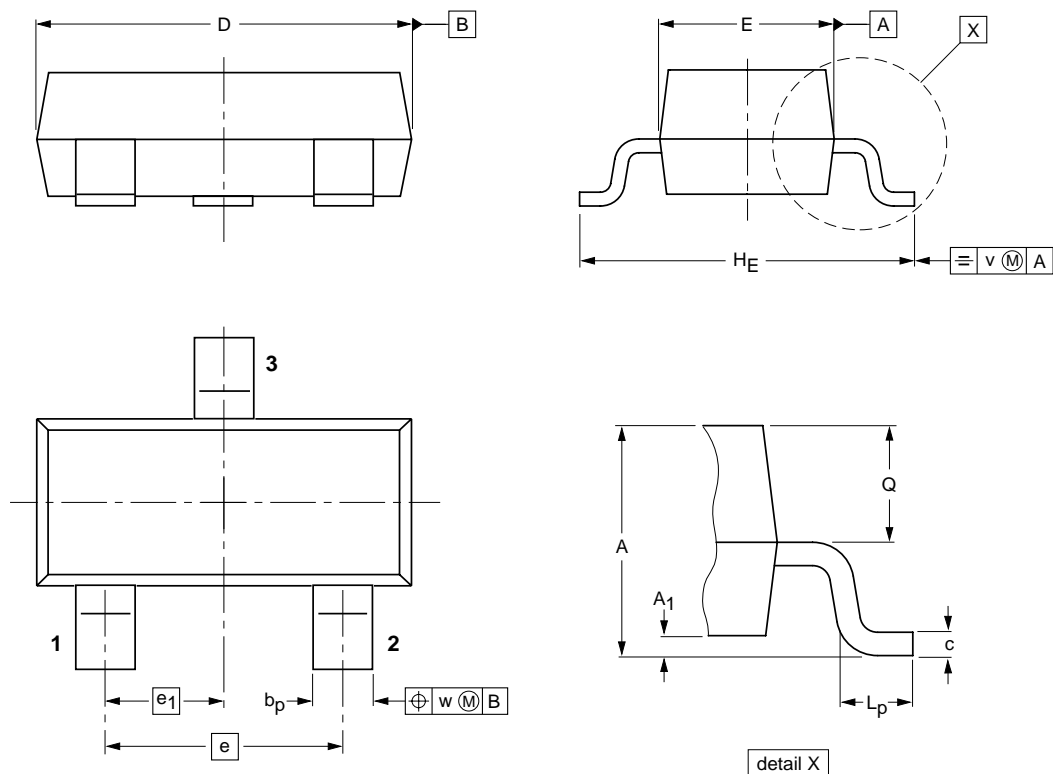
PNP general purpose transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT23		TO-236AB			97-02-28 99-09-13

PNP general purpose transistor

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DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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